

S/N 09/944981

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Examiner: Walter Lindsay

Serial No.: 09/944981

Group Art Unit: 2812

Filed: August 30, 2001

Docket: 1303.021US1

CRYSTALLINE OR AMOPHOUS MEDIUM-K GATE OXIDES, Y203 AND Gd203

MS Amendment
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INFORMATION DISCLOSURE STATEMENT

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants have included the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p). Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.

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By their Representatives,

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Date 6-18-04

By D.C.P.

David C. Peterson
Reg. No. 47,857

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 18th day of June, 2004.

Amy Moriarty
Name

Amy Moriarty
Signature

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
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Application Number	09/944981
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First Named Inventor	Ahn, Kie
Group Art Unit	2812
Examiner Name	Lindsay, Walter

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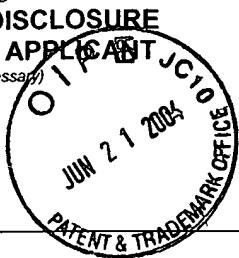
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Application Number	09/944981	<i>RECEIVED</i>
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Group Art Unit	2812	<i>TECH CENTER 2800</i>
Examiner Name	Lindsay, Walter	

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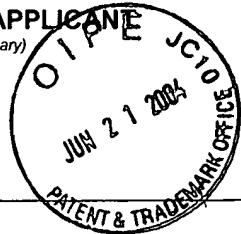
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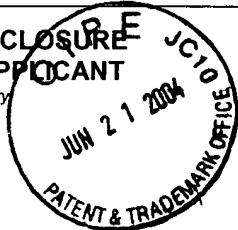
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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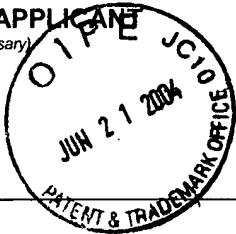
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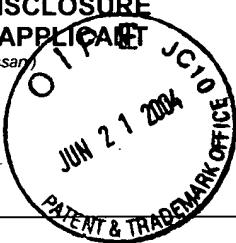
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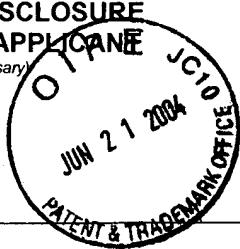
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